

*Concld
C1
B1
concld*

of said cathode material; and

an emitting layer over each of said at least one tip, wherein said emitting layer is comprised of a metal silicide and has a thickness between 50 and 3000 angstroms.

Please REWRITE claim 39 as follows:

*sub
C1
B1*

39. (AMENDED) A large area passive matrix cold cathode field emission display device comprising:

cathode material on a semiconductor substrate;

at least one emitter tip with a sharp profile for emitting electrons formed out of said cathode material;

an emitting layer over each of said at least one tip, wherein said emitting layer is comprised of a metal silicide and has a thickness between 50 and 3000 angstroms.
